

**AMENDMENTS TO THE CLAIMS**

1. (Currently Amended) A method of fabricating a capacitor for a semiconductor device, comprising the steps of:

a) forming a sacrificial layer in the height of the capacitor on a substrate, wherein an etch rate of an upper portion of the sacrificial layer is lower than that of a lower portion of the sacrificial layer, wherein the sacrificial layer is a TEOS layer and the sacrificial layer is formed in response to a RF power, an O<sub>2</sub> flow, and a spacing between the substrate and the shower head, and the lower portion of the sacrificial layer has a higher wet etching rate than the upper portion of the sacrificial layer does;

b) forming a trench by selectively eliminating the sacrificial layer by a wet etch process;

c) forming a bottom electrode in the trench;

d) eliminating the sacrificial layer;

e) forming a dielectric thin film on the bottom electrode; and

f) forming the top electrode on the dielectric thin film.

Claims 2-3 (Canceled).

4. (Currently Amended) The method of fabricating the capacitor as recited in claim 3~~1~~, wherein the sacrificial layer is deposited in thickness ranging from about 10000 Å to about 25000 Å.